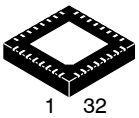
3.3 V Differential 1:10 Fanout Clock Driver with HCSL Outputs

NB3N111K



QFN32
MN SUFFIX
CASE 488AM

Description

The NB3N111K is a differential 1:10 Clock fanout buffer with High−speed Current Steering Logic (HCSL) outputs optimized for ultra low propagation delay variation. The NB3N111K is designed with PCI Express HCSL clock distribution and FBDIMM applications in mind.

Inputs can directly accept differential LVPECL, LVDS, and HCSL signals per Figures 7, 8, and 9. Single−ended LVPECL, HCSL, LVCMOS, or LVTTL levels are accepted with a proper external V_{th} reference supply per Figures 4 and 10. Input pins incorporate separate internal 50 Ω termination resistors allowing additional single ended system interconnect flexibility.

Output drive current is set by connecting a 475 Ω resistor from IREF (Pin 1) to GND per Figure 6. Outputs can also interface to LVDS receivers when terminated per Figure 11.

The NB3N111K specifically guarantees low output−to−output skew. Optimal design, layout, and processing minimize skew within a device and from device to device. System designers can take advantage of the NB3N111K's performance to distribute low skew clocks across the backplane or the motherboard.

Features

- Typical Input Clock Frequency 100, 133, 166, or 400 MHz
- 220 ps Typical Rise and Fall Times
- 800 ps Typical Propagation Delay
- Δtpd 100 ps Maximum Propagation Delay Variation per Diff Pair
- 0.1 ps Typical RMS Additive Phase Jitter
- LVDS Output Levels Optional with Interface Termination
- Operating Range: V_{CC} = 3.0 V to 3.6 V with GND = 0 V
- Typical HCSL Output Levels (700 mV Peak−to−Peak)
- LVDS Output Levels with Interface Termination
- These are Pb−Free Devices

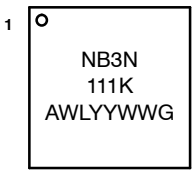
Applications

- Clock Distribution
- PCIe I, II, III
- Networking
- High End Computing
- Routers

End Products

- Servers
- FBDIMM Memory Card

MARKING DIAGRAM*



A	= Assembly Location
WL	= Wafer Lot
YY	= Year
WW	= Work Week
G	= Pb−Free Package

*For additional marking information, refer to Application Note AND8002/D.

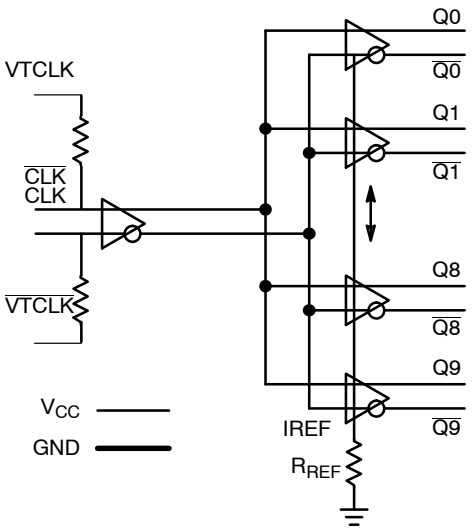


Figure 1. Simplified Logic Diagram

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

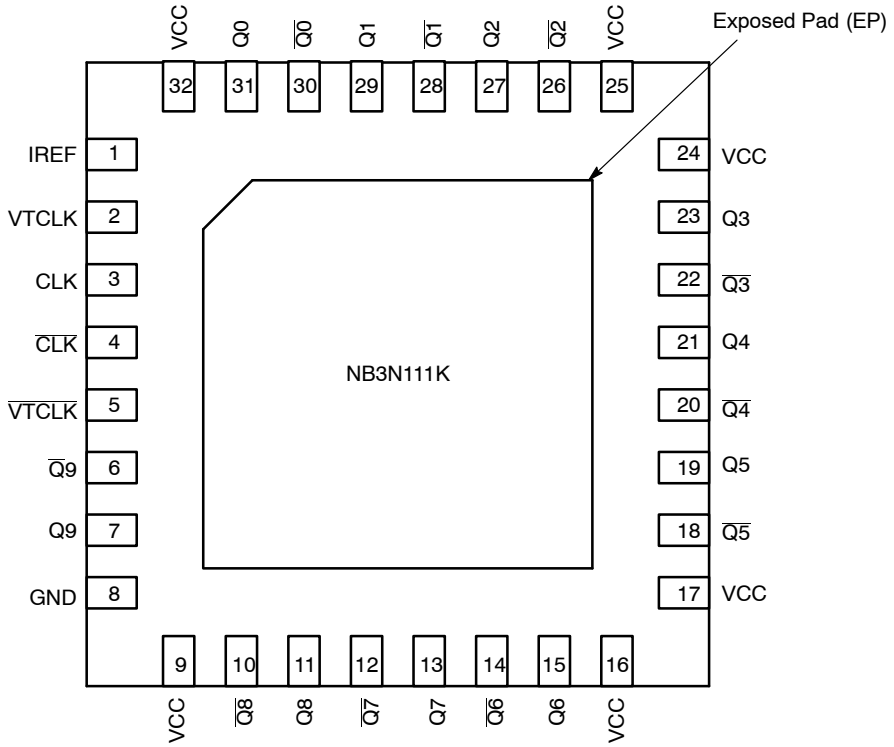


Figure 2. Pinout Configuration (Top View)

Table 1. PIN DESCRIPTION

Pin	Name	I/O	Description
1	IREF		Use the IREF pin to set the output drive. Connect a 475 Ω RREF resistor from the IREF pin to GND to produce 2.6 mA of IREF current. A current mirror multiplies IREF by a factor of 5.4x to force 14 mA through a 50 Ω output load. See Figures 6 and 12.
2, 5	VTCLK, $\overline{\text{VTCLK}}$	–	Internal 50 Ω Termination Resistor connection Pins. In the differential configuration when the input termination pins are connected to the common termination voltage, and if no signal is applied then the device may be susceptible to self−oscillation.
3	CLK	LVPECL, HCSL, LVDS Input	Clock and Data (TRUE) Input
4	$\overline{\text{CLK}}$	LVPECL, HCSL, LVDS Input	Clock and Data (INVERT) Input
6, 10, 12, 14, 18, 20, 22, 26, 28, 30	$\overline{\text{Q[9−0]}}$	HCSL or LVDS (Note 1) Output	Output (INVERT) (Note 1)
7, 11, 13, 15, 19, 21, 23, 27, 29, 31	Q[9−0]	HCSL or LVDS (Note 1) Output	Output (TRUE) (Note 1)
8	GND	–	Supply Ground. GND pin must be externally connected to power supply to guarantee proper operation.
9, 16, 17, 24, 25, 32	VCC	–	Positive Voltage Supply pin. VCC pins must be externally connected to a power supply to guarantee proper operation.
Exposed Pad	EP	GND	Exposed Pad. The thermally exposed pad (EP) on package bottom (see case drawing) must be attached to a sufficient heat−sinking conduit for proper thermal operation and electrically connected to the circuit board ground (GND).

1. Outputs can also interface to LVDS receiver when terminated per Figure 11.

Table 2. ATTRIBUTES

Characteristic	Value
ESD Protection Human Body Model Machine Model	 >2 kV 200 V
Moisture Sensitivity (Note 2) QFN32	 Level 1
Flammability Rating Oxygen Index: 28 to 34	 UL 94 V−0 @ 0.125 in
Transistor Count	286
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

2. For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS (Note 3)

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	Positive Power Supply	GND = 0 V		4.6	V
V_I	Positive Input	GND = 0 V		GND − 0.3 ≤ V_I ≤ V_{CC}	V
VINPP	Differential Input Voltage			V_{CC}	V
I_{OUT}	Output Current	Continuous Surge		50 100	mA mA
T_A	Operating Temperature Range	QFN32		−40 to +85	°C
T_{stg}	Storage Temperature Range			−65 to +150	°C
θ_{JA}	Thermal Resistance (Junction−to−Ambient) (Note 3)	0 lfpm 500 lfpm	QFN32 QFN32	31 27	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction−to−Case)	2S2P (Note 3)	QFN32	12	°C/W
T_{sol}	Wave Solder Pb−Free			265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

3. JEDEC standard 51−6, multilayer board − 2S2P (2 signal, 2 power) with 8 filled thermal vias under exposed pad.

Table 4. DC CHARACTERISTICS (V_{CC} = 3.0 V to 3.6 V, T_A = −40°C to +85°C Note 4)

Symbol	Characteristic	Min	Typ	Max	Unit
I_{GND}	GND Supply Current (All Outputs Loaded)		60	90	mA
I_{CC}	Power Supply Current (All Outputs Loaded)		210	260	mA
I_{IH}	Input HIGH Current		2.0	150	μA
I_{IL}	Input LOW Current	−150	−2.0		μA
R_{TIN}	Internal Input Termination Resistor	45	50	55	Ω
DIFFERENTIAL INPUT DRIVEN SINGLE−ENDED					
V_{th}	Input Threshold Reference Voltage Range (Note 5)	350		V_{CC} − 1000	mV
V_{IH}	Single − Ended Input HIGH Voltage	V_{th} + 150		V_{CC}	mV
V_{IL}	Single − Ended Input LOW Voltage	GND		V_{th} − 150	mV
DIFFERENTIAL INPUTS DRIVEN DIFFERENTIALLY (Figures 7, 8 and 9)					
V_{IHD}	Differential Input HIGH Voltage	425		V_{CC} − 850	mV
V_{ILD}	Differential Input LOW Voltage	GND		V_{CC} − 1000	mV
V_{ID}	Differential Input Voltage (V_{IHD} − V_{ILD})	150		V_{CC} − 850	mV
V_{CMR}	Input Common Mode Range	350		V_{CC} − 1000	mV
HCSL OUTPUTS (Figure 4)					
V_{OH}	Output HIGH Voltage	600	740	900	mV
V_{OL}	Output LOW Voltage	−150	0	150	mV

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

4. Measurements taken with outputs loaded 50 Ω to GND. Connect a 475 Ω resistor from IREF (Pin 1) to GND. See Figure 6.
5. V_{th} is applied to the complementary input when operating in single ended mode per Figure 4.

Table 5. AC CHARACTERISTICS V_{CC} = 3.0 V to 3.6 V, GND = 0 V; −40°C to +85°C (Note 6)

Symbol	Characteristic	Min	Typ	Max	Unit
V_{OUTPP}	Output Voltage Amplitude (@ $V_{INPPmin}$) $f_{in} \le 400$ MHz		725	1000	mV
t_{PLH}, t_{PHL}	Propagation Delay (See Figure 3a) CLK/$\overline{CLK}$ to Qx/$\overline{Qx}$	550	800	1100	ps
Δt_{PLH}, Δt_{PHL}	Propagation Delay Variation Per Each Diff Pair (Note 7) (See Figure 3a) CLK/$\overline{CLK}$ to Qx/$\overline{Qx}$			100	ps
t_{SKEW}	Duty Cycle Skew (Note 8) Within −Device Skew Device to Device Skew (Note 9)			20 100 150	ps
$t_{JIT}\theta$	Additive Integrated Phase Jitter at Fc = 100 MHz (Note 10)		0.1		ps
V_{INPP}	Input Voltage Swing/Sensitivity (Differential Configuration)	0.150		V_{CC} − 0.85	V
V_{CROSS}	Absolute Crossing Magnitude Voltage (See Figure 3b)	250		550	mV
ΔV_{CROSS}	Variation in Magnitude of V_{CROSS} (See Figure 3b)			150	mV
t_r , t_f	Absolute Magnitude in Output Risetime and Falltime (from 175 mV to 525 mV) (See Figure 3b) Qx, $\overline{Qx}$	150	220	400	ps
Δtr, Δtf	Variation in Magnitude of Risetime and Falltime (Single−Ended) (See Figure 3b) Qx, $\overline{Qx}$			125	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

6. Measured by forcing V_{INPP} (MIN) from a 50% duty cycle. Measurement taken with all outputs loaded 50 Ω to GND. Connect a 475 Ω resistor from IREF (Pin 1) to GND. See Figure 6.
7. Measured from the input pair crosspoint to each single output pair crosspoint across temp and voltage ranges per Figure 3.
8. Duty cycle skew is measured between differential outputs using the deviations of the sum of T_{pw-} and T_{pw+}.
9. Skew is measured between outputs under identical transition conditions @ 50 MHz.
10. Phase noise integrated from 12 kHz to 20 MHz.

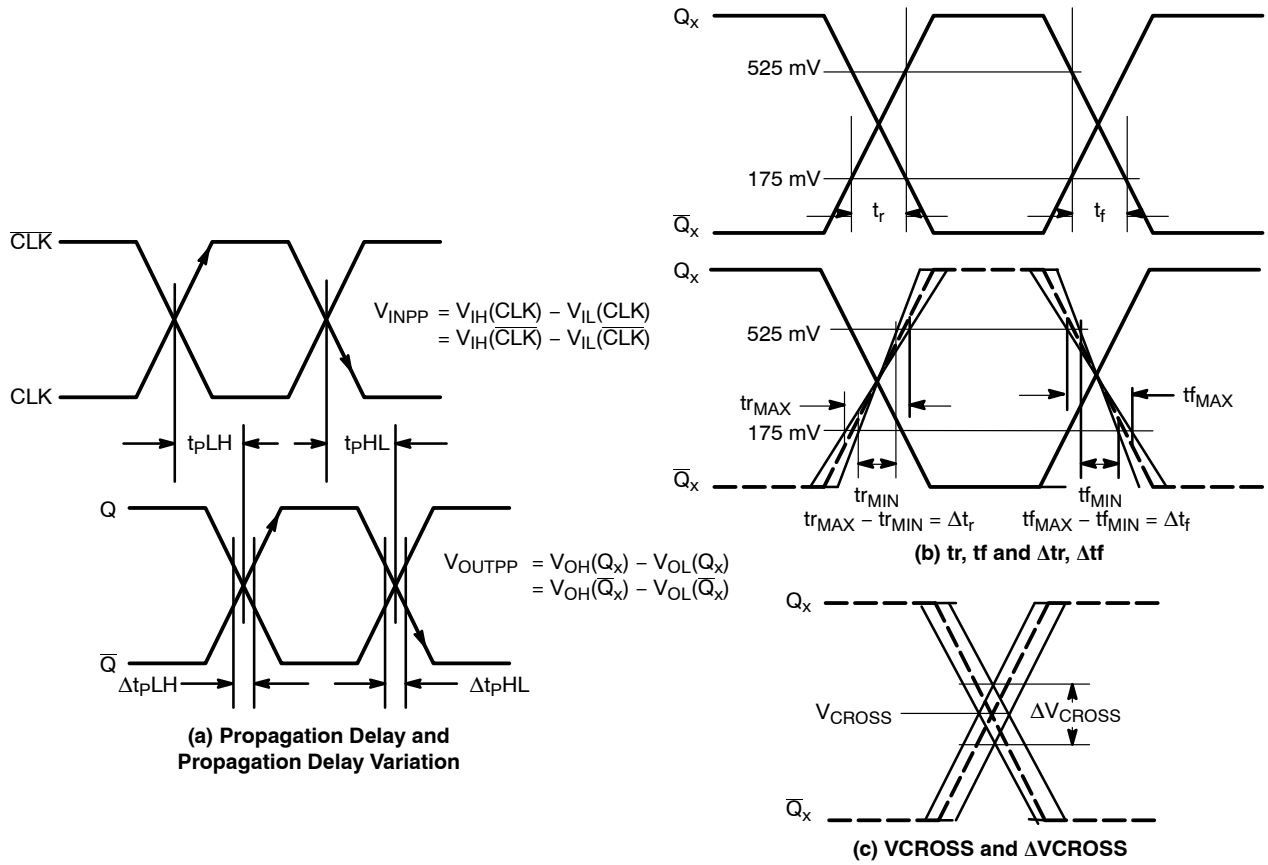


Figure 3. AC Reference Measurement

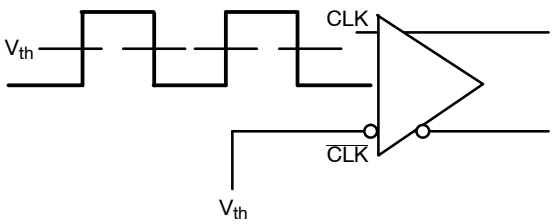


Figure 4. Single−Ended Interconnect V_{th} Reference Voltage

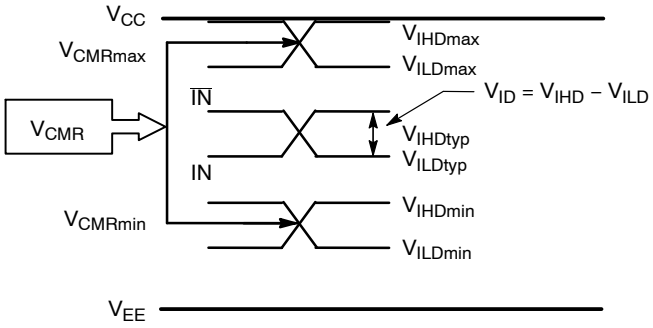
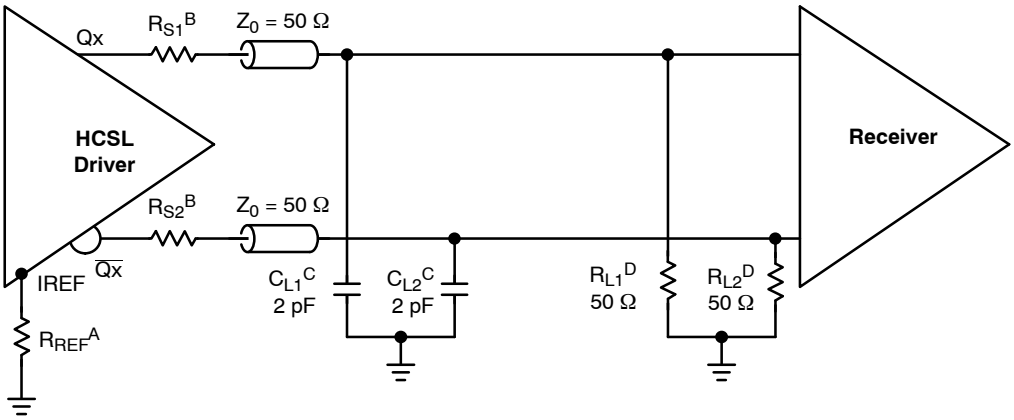
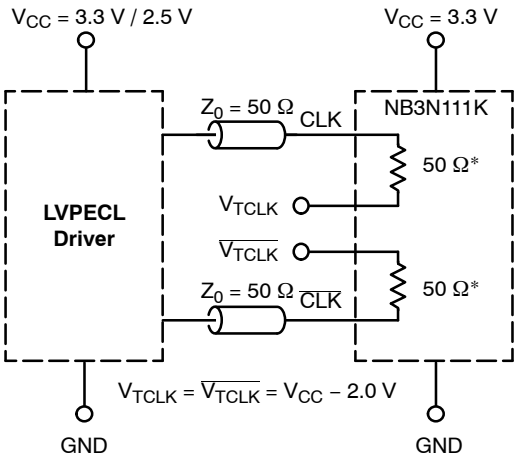


Figure 5. V_{th} Diagram



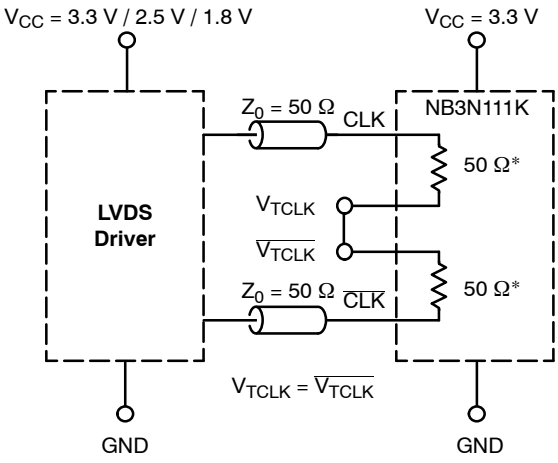
A. Connect 475 Ω resistor R_{REF} from IREF pin to GND.
B. R_{S1}, R_{S2}: 0 Ω for Test and Evaluation. Select to Minimizing Ringing.
C. C_{L1}, C_{L2}: Receiver Input Simulation (for test only not added to application circuit) Load capacitance only.
D. D_{L1}, D_{L2} Termination and Load Resistors Located at Receiver Inputs.

Figure 6. Typical Termination Configuration for Output Driver and Device Evaluation



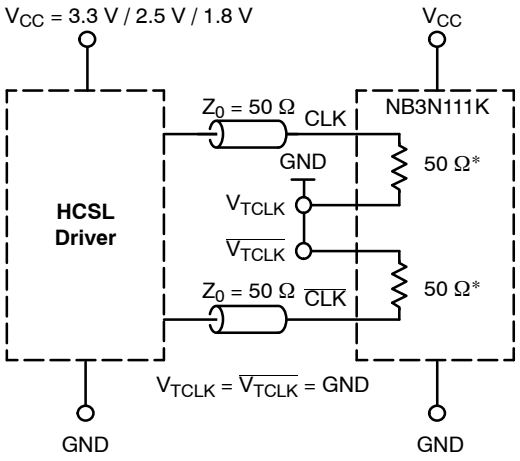
*RTIN, Internal Input Termination Resistor

Figure 7. LVPECL Interface



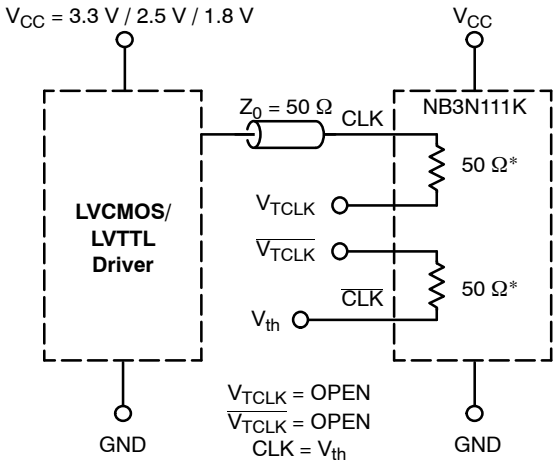
*RTIN, Internal Input Termination Resistor

Figure 8. LVDS Interface



*RTIN, Internal Input Termination Resistor

Figure 9. Standard 50 Ω Load HCSL Interface



*RTIN, Internal Input Termination Resistor

Figure 10. LVCMOS/LVTTL Interface

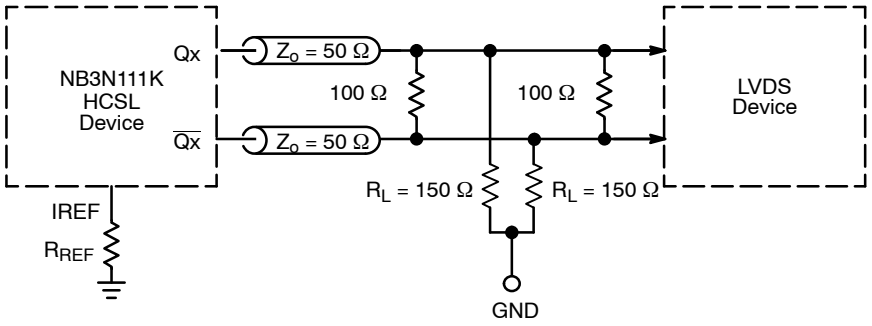


Figure 11. HCSL Interface Termination to LVDS

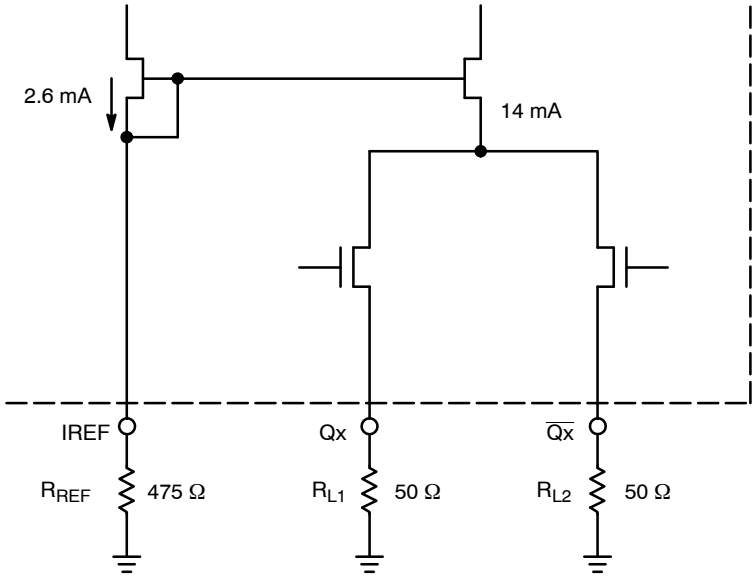


Figure 12. HCSL Simplified Output Structure

ORDERING INFORMATION

Device	Package	Shipping†
NB3N111KMNR4G	QFN32 (Pb−Free)	1000 / Tape & Reel

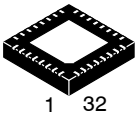
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

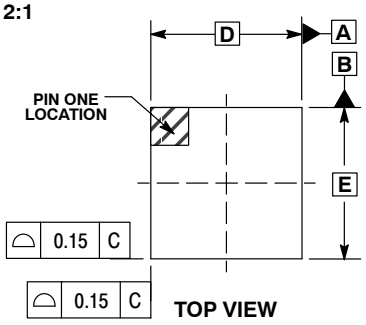
ON Semiconductor®

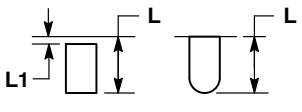
QFN32 5x5, 0.5P
CASE 488AM
ISSUE A

DATE 23 OCT 2013

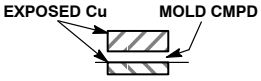


SCALE 2:1

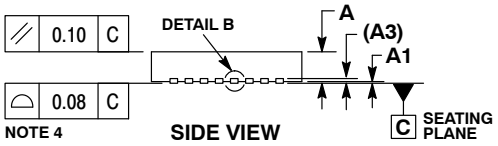


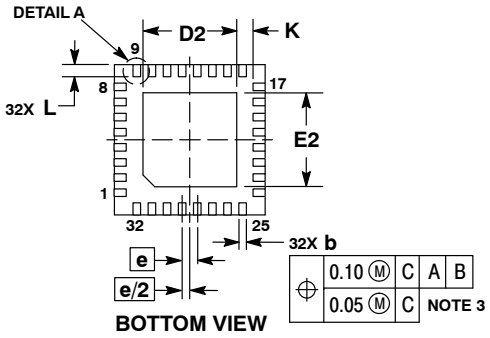


DETAIL A
ALTERNATE TERMINAL CONSTRUCTIONS



DETAIL B
ALTERNATE CONSTRUCTION

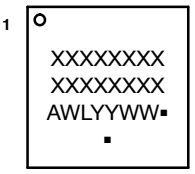




NOTES:
1. DIMENSIONS AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS	
DIM	MIN	MAX
A	0.80	1.00
A1	---	0.05
A3	0.20 REF	
b	0.18	0.30
D	5.00 BSC	
D2	2.95	3.25
E	5.00 BSC	
E2	2.95	3.25
e	0.50 BSC	
K	0.20	---
L	0.30	0.50
L1	---	0.15

GENERIC MARKING DIAGRAM*

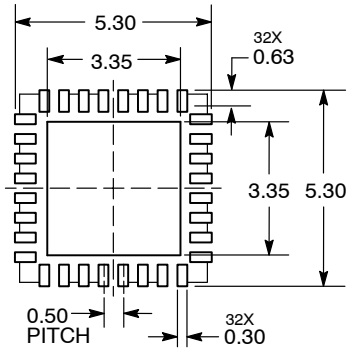


XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking.
Pb−Free indicator, "G" or microdot " ▪", may or may not be present.

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSION: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	**98AON20032D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**QFN32 5x5 0.5P**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
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For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales